

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

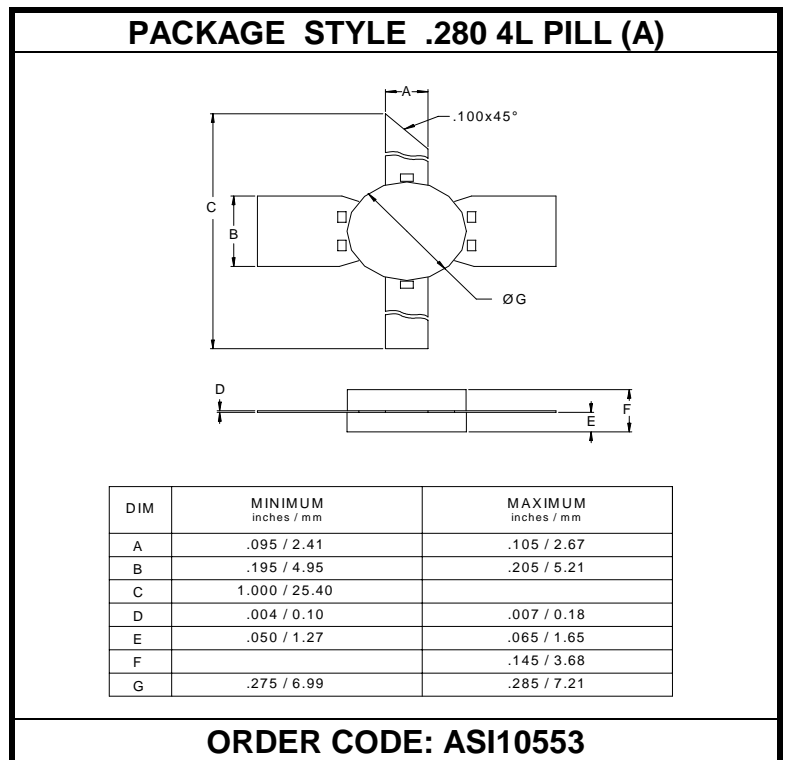
The **ASI AVD002P** is Designed for Class C, DME/TACAN Applications up to 1150 MHz.

**FEATURES:**

- Class C Operation
- $P_G = 9.0$  dB at 2.0 W/1150 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	250 mA
$V_{CC}$	37 V
$P_{DISS}$	10 W @ $T_C \leq 100$ °C
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	10 °C/W


**CHARACTERISTICS**  $T_C = 25$  °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 1.0$ mA	45			V
$BV_{CER}$	$I_C = 5.0$ mA $R_{BE} = 10$ $\Omega$	45			V
$BV_{EBO}$	$I_E = 1.0$ mA	3.5			V
$I_{CES}$	$V_{CE} = 35$ V			1.0	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 100$ A	30		300	---
$P_G$	$V_{CC} = 35$ V $P_{OUT} = 2.0$ W $f = 1025 - 1150$ MHz	9.0			dB
$\eta_c$		35			%